



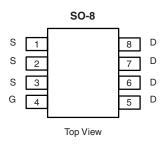
# N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}\left(\Omega\right)$	I <sub>D</sub> (A)		
30	0.024 at V <sub>GS</sub> = 10 V	8.1		
	$0.033$ at $V_{GS} = 4.5 \text{ V}$	6.9		

#### **FEATURES**

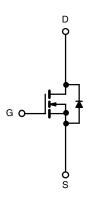
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFETs
- Compliant to RoHS Directive 2002/95/EC





Ordering Information: Si9410BDY-T1-E3 (Lead (Pb)-free)

Si9410BDY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b>	A = 25 °C, unle	ss otherwise n	oted			
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30		٧	
Gate-Source Voltage		V <sub>GS</sub>	± 20			
Opation - Dupin Orange /T 150 00\8	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	8.1	6.2	٨	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		6.5	5.0		
Pulsed Drain Current (10 µs Pulse Width)		I <sub>DM</sub>	30		Α	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	2.1	1.2		
	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	2.5	1.5	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		1.6	0.9	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manifestore bounding to Aughing 18	t ≤ 10 s	- R <sub>thJA</sub>	40	50	°C/W
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		70	85	
Maximum Junction-to-Foot	Steady State	$R_{thJF}$	20	24	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

# Vishay Siliconix



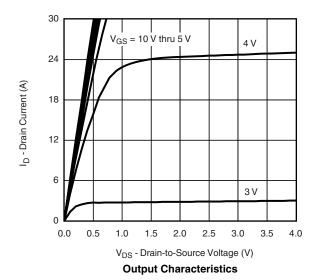
<b>SPECIFICATIONS</b> T <sub>J</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static				•			
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250 \mu A$ 1.0		3.0	V		
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1	μΑ	
		$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α	
Drain-Source On-State Resistance <sup>a</sup>	В	$V_{GS} = 10 \text{ V}, I_D = 8.1 \text{ A}$	0.019		0.024	- 0	
	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 6.9 \text{ A}$		0.026	0.033	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 8.1 A		20		S	
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 2.1 A, V <sub>GS</sub> = 0 V		0.8	1.2	V	
Dynamic <sup>b</sup>			•	•			
Total Gate Charge	$Q_g$			15	23		
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 8.1 \text{ A}$		3.2		nC	
Gate-Drain Charge	$Q_{gd}$			2.5			
Turn-On Delay Time	t <sub>d(on)</sub>			10	15		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 15 $\Omega$		15	25		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 1 \text{ A, V}_{GEN} = 10 \text{ V, R}_g = 6 \Omega$		30	45	ns	
Fall Time	t <sub>f</sub>			11	20		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.1 A, dI/dt = 100 A/μs		25	50		

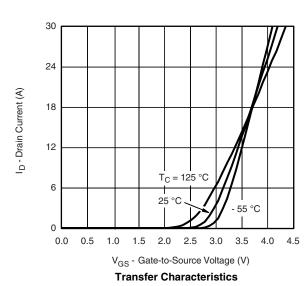
#### Notes:

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



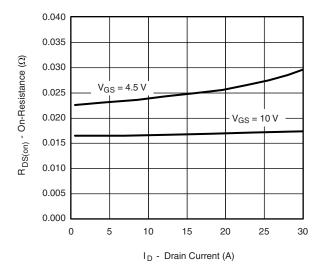




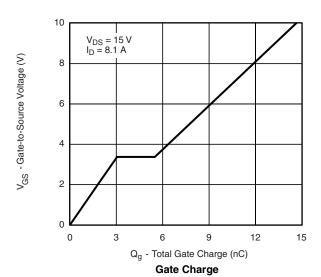




## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



On-Resistance vs. Drain Current



T<sub>J</sub> = 150 °C

T<sub>J</sub> = 150 °C

T<sub>J</sub> = 25 °C

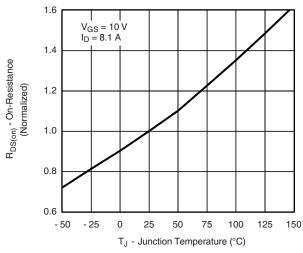
T<sub>J</sub> = 25 °C

V<sub>SD</sub> - Source-to-Drain Voltage (V)

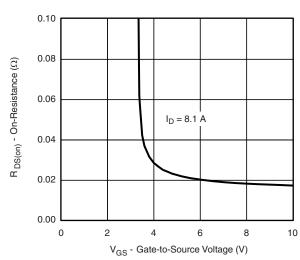
Source-Drain Diode Forward Voltage

1200 1000 C<sub>iss</sub> C - Capacitance (pF) 800 600 400 Coss 200  $C_{rss}$ 0 0 10 15 20 25 30

 $V_{DS}$  - Drain-to-Source Voltage (V) **Capacitance** 



On-Resistance vs. Junction Temperature



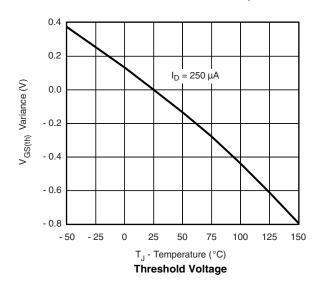
On-Resistance vs. Gate-to-Source Voltage

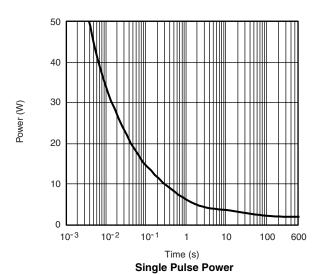
Is - Source Current (A)

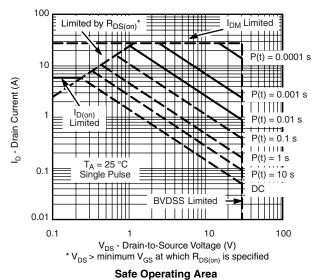
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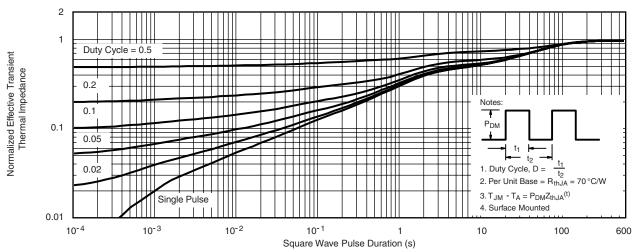
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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





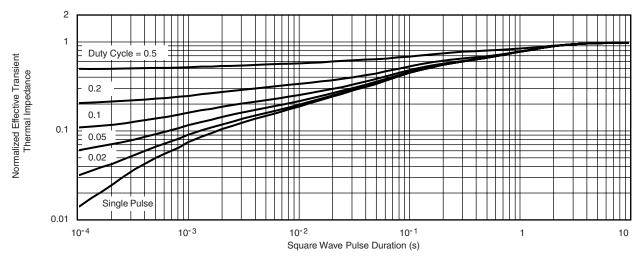




Normalized Thermal Transient Impedance, Junction-to-Ambient



## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

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